



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO.,LTD.

ESD静电浪涌保护二极管

型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSHC3D15V1U	15	16.5	20	80	1横+TDN	SOD-323		
FSLC3D3V1B	3.3	4.5	8.5	19	CC	SOD-323		
FSLC3D3V1BA	3.3	4.5	8.5	14	CC/3B	SOD-323	GBLC03C-N	BORN伯恩半导体
FSLC3D3V1BA	3.3	4.5	8.5	14	CC/3C	SOD-323	RLSD32A031LC	RUILON(瑞隆源)
FSLC3D3V1BA	3.3	4.5	8.5	14	CC/3C	SOD-323	UCD32C03L01	Brightking台湾君耀
FSLC3D3V1BA	3.3	4.5	8.5	14	CC/3C	SOD-323	ESDSL3V3D3B-TP	MCC(美微科)
FSLC3D3V1BB	3	3.5	8	10	CC	SOD-323		
FSLC3D3V1BC	3	3.5	8	15	CC	SOD-323		
FSLC3D3V1BL	3	3.8	8.5	20	CC	SOD-323		
FSLC3D3V1UA	3.3	4.5	8.5	14	S3	SOD-323	CESD3V3D3	CJ(江苏长电/长晶)
FSLC3D3V1UA	3.3	4.5	8.5	14	S3	SOD-323	ESD7351HT1G	ON(安森美)
FSLC3D3V1UA	3.3	4.5	8.5	14	S3	SOD-323	PESD3V3U1UA, 115	Nexperia(安世)
ES05D1HA03	5	5.6	16	20	05C	SOD-323		
FSLC3D5V1B	5	6.5	9.5	18	AC	SOD-323		
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	ESD5V0B03-323	TECH PUBLIC(台舟)
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	GBLC05C-TP	TECH PUBLIC(台舟)
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	BSD3C361V	BORN伯恩半导体
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	SESD3Z5CL	SINO-IC(光宇睿芯)
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	RLSD32A051LC	RUILON(瑞隆源)
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	UCD32C05L01	Brightking台湾君耀
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	UCD32C05L01-AT	Brightking台湾君耀
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	UBD32C05L01	Brightking台湾君耀
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	ESD05V32D-LC	TECH PUBLIC(台舟)
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	PESD5V0U1BA-TP	TECH PUBLIC(台舟)
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	TPDESD5V0U1BA	TECH PUBLIC(台舟)



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Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSLC3D5V1BA	5	6.5	9.5	12	AC/5C	SOD-323	GBLC05C	TECH PUBLIC(台舟)
FSLC3D5V1BB	5	6.5	9.5	8	3B/LC	SOD-323		
FSLC3D5V1BC	5	6.5	8.5	6	AC	SOD-323		
FSLC3D8V1B	8	8.5	12	14	BC	SOD-323		
FSLC3D8V1BA	8	8.5	12	10	BC/8C	SOD-323	ESDLC8V0D3B	Yint(音特电子)
FSLC3D8V1BA	8	8.5	12	10	BC/8C	SOD-323	UCD32C08L01	Brightking(君耀)
FSLC3D12V1B	12	13.3	19	9	DC	SOD-323		
FSLC3D12V1BA	12	13.3	19	8	DC/2C	SOD-323	UCD32C12L01	Brightking(君耀)
FSLC3D12V1BA	12	13.3	19	8	DC/2C	SOD-323	CESD323LC12VB-M	CREATEK(达晶微)
FSLC3D12V1BA	12	13.3	19	8	DC/2C	SOD-323	GBLC12C-MS	MSKSEMI(美森科)
FSLC3D12V1BA	12	13.3	19	8	DC/2C	SOD-323	ESDLC12VD3B	Yint(音特电子)
FSLC3D15V1B	15	16.5	24	7	EC	SOD-323		
FSLC3D15V1BA	15	16.5	24	6	EC	SOD-323	UDD32C15L01	Brightking(君耀)
FSLC3D15V1BA	15	16.5	24	6	EC	SOD-323	UCD32C15L01	Brightking(君耀)
FSLC3D18V1B	18	20	30	6	FC	SOD-323		
FSLC3D24V1B	24	26	34	5	HC	SOD-323		
FSLC3D24V1BA	24	26	34	3	HC	SOD-323	SDD32C24L01	Brightking(君耀)
FSLC3D24V1BA	24	26	34	3	HC	SOD-323	UDD32C24L01	Brightking(君耀)
FSLC3D24V1BA	24	26	34	3	HC	SOD-323	SELC24CI	SEMIWARE(赛米微尔)
FSLC3D24V1BA	24	26	34	3	HC	SOD-323	TPE32C24L01	TECH PUBLIC(台舟)
FSLC3D24V1BA	24	26	34	3	HC	SOD-323	PDYL240B-SOD323	TECH PUBLIC(台舟)
FSLC3D24V1BA	24	26	34	3	HC	SOD-323	RLSD32A241LC	RUILON(瑞隆源)
FSLC3D24V1BA	24	26	34	3	HC	SOD-323	GBLC24C	Prottek Devices
FSLC3D24V1BA	24	26	34	3	HC	SOD-323	UCD32C24L01	Brightking(君耀)
FSLC3D36V1B	36	38	55	3	KC	SOD-323		



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSLC3D5V1UA	5	6.5	9.5	12	2横+S5	SOD-323		
FSLC3D8V1UA	8	8.5	12	10	2横+S8	SOD-323		
FSLC3D12V1UA	12	13.3	19	8	2横+S12	SOD-323		
FSLC3D15V1UA	15	16.5/26	24	6	2横+S15	SOD-323		
FSLC3D24V1UA	24	26	34	3	2横+S24	SOD-323		
FSNC3D3V1U	3.3	4.5	19	24	1横+03W	SOD-323	SD05T1G	ON(安森美)
FSNC3D3V1U	3.3	4.5	19	24	1横+03W	SOD-323	BSD3A031V	BORN伯恩半导体
FSNC3D3V1UA	3.3	4.5	8	25	1横+03W	SOD-323		
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	CESD5V0D3	CJ(江苏长电/长晶)
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	SDD32A05L01	Brightking(君耀)
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	LES3Z5.0T1G	LRC(乐山无线电)
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	SESD3Z5V	SINO-IC(光宇睿芯)
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	RLSD32A051V	RUILON(瑞隆源)
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	ESD3Z5.0	AnBon(台湾安邦)
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	SD05.TCT	UMW(友台半导体)
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	CESD323NC5VU-M	CREATEK(达晶微)
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	BSD3A051V	BORN伯恩半导体
FSNC3D5V1U	5	6.5	20	20	1横+05W	SOD-323	PESDNC3D5VU	Prisemi 芯导
FSNC3D5V1UB	5	5.5	8	80	1横+HU	SOD-323		
FSNC3D12V1U	12	13.3	33	12	1横+12W	SOD-323	CESD12VD3 ZC	CJ(江苏长电/长晶)
FSNC3D12V1U	12	13.3	33	12	1横+12W	SOD-323	SD12T1G	ON(安森美)
FSNC3D12V1U	12	13.3	33	12	1横+12W	SOD-323	RLSD32A121V	RUILON(瑞隆源)
FSNC3D12V1U	12	13.3	33	12	1横+12W	SOD-323	SESD3Z12V	SINO-IC(光宇睿芯)
FSNC3D12V1U	12	13.3	33	12	1横+12W	SOD-323	ESD12VD3-TP	MCC(美微科)
FSNC3D12V1U	12	13.3	33	12	1横+12W	SOD-323	SDD32A12L01	Brightking(君耀)



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Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC3D12V1U	12	13.3	33	12	1横+12W	SOD-323	CESD323NC12VU-M	CREATEK(达晶微)
FSNC3D12V1U	12	13.3	33	12	1横+12W	SOD-323	PJSD12W	PANJIT(强茂)
FSNC3D15V1U	15	16.5	50	9	1横+15W	SOD-323	RLSD32A151V	RUILON(瑞隆源)
FSNC3D15V1U	15	16.5	50	9	1横+15W	SOD-323	PJSD15W	PANJIT(强茂)
FSNC3D24V1U	24	26	60	6	1横+24W	SOD-323	PJSD24W	PANJIT(强茂)
FSNC3D24V1U	24	26	60	6	1横+24W	SOD-323	RLSD32A241V	RUILON(瑞隆源)
FSNC3D24V1U	24	26	60	6	1横+24W	SOD-323	SD24	Leiditech(雷卯电子)
FSNC3D36V1U	36	45	50	3	1横+36W	SOD-323	CESD36VD3	CJ(江苏长电/长晶)
FSNC3D36V1U	36	45	50	3	1横+36W	SOD-323	RLSD32A361V	RUILON 瑞隆源
FSNC3D36V1U	36	45	50	3	1横+36W	SOD-323	PJSD36W	PANJIT(强茂)
FSNC3D36V1UA	36	40	50	2.5	1横+36W	SOD-323		
FSNC3D3V1B	3.3	4.5	8.5	24	2A	SOD-323		
FSNC3D3V1BA	3.3	4.5	8.5	16	5横+AB	SOD-323		
FSNC3D3V1BB	3.3	3.5	8	20	2A	SOD-323		
FSNC3D3V1BC	3.3	3.5	8	30	2A	SOD-323		
FSNC3D3V1BD	3.3	3.7	7	6	3CW	SOD-323		
FSNC3D5V1B	5	6.5	9.5	20	2B	SOD-323		
FSNC3D5V1BC	5	6	11	8	E6/H	SOD-323	CESDBLC5V0D3	CJ(江苏长电/长晶)
FSNC3D5V1BC	5	6	11	8	E6/B5	SOD-323	ESD5V0D3B-TP	MCC(美微科)
FSNC3D5V1BC	5	6	11	8	E6/1K	SOD-323	PESD5V0V1BA	Nexperia(安世)
FSNC3D5V1BC	5	6	11	8	E6/A/V	SOD-323	DESD5V0S1BA-7	达尔-Diodes
FSNC3D5V1BB	5	6	18	16	5横+E6	SOD-323	PESD5V0L1BA, 115	Nexperia(安世)
FSNC3D5V1BB	5	6	18	16	5横+E6	SOD-323	PESD5V0V1BA-N	BORN伯恩半导体
FSNC3D5V1BB	5	6	18	16	5横+E6	SOD-323	TPCESD5V0D3	TECH PUBLIC(台舟)
FSNC3D5V1BB	5	6	18	16	5横+E6	SOD-323	ESDLC5V0D3B-TP	MCC(美微科)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC3D5V1BA	5	6.5	9.5	15	5横+AC	SOD-323	RLSD32A051C	RUILON(瑞隆源)
FSNC3D5V1BA	5	6.5	9.5	15	5横+AC	SOD-323	CESDB5V0D3	CJ(江苏长电/长晶)
FSNC3D5V1BA	5	6.5	9.5	15	5横+AC	SOD-323	SDD32C05L01	Brightking(君耀)
FSNC3D5V1BA	5	6.5	9.5	15	5横+AC	SOD-323	PESD5V0S1BAF	Nexperia(安世)
FSNC3D5V1BA	5	6.5	9.5	15	5横+AC	SOD-323	ESDB5V0D3	TECH PUBLIC(台舟)
FSNC3D8V1B	8	8.5	11	15	2C	SOD-323		
FSNC3D8V1BA	8	8.5	11	12	2C	SOD-323		
FSNC3D12V1B	12	13.3	20	12	2D/AD/K	SOD-323		
FSNC3D12V1BA	12	13.3	35	8	5横+AD	SOD-323	PESD12VL1BA, 115	Nexperia(安世)
FSNC3D12V1BA	12	13.3	35	8	5横+AD	SOD-323	SESD3Z12C	SINO-IC(光宇睿芯)
FSNC3D12V1BA	12	13.3	35	8	5横+AD	SOD-323	RLSD32A121C	RUILON(瑞隆源)
FSNC3D12V1BA	12	13.3	35	8	5横+AD	SOD-323	CESD323NC12VB	CREATEK(达晶微)
FSNC3D12V1BC	12	13.3	16	6	12B	SOD-323		
FSNC3D15V1B	15	16.5	25	9	2J	SOD-323		
FSNC3D15V1BA	15	16.5	45	6	5横+AE/15B	SOD-323	PESD15VL1BA, 115	Nexperia(安世)
FSNC3D15V1BA	15	16.5	45	6	5横+AE/15B	SOD-323	PESD1LIN, 115	Nexperia(安世)
FSNC3D15V1BA	15	16.5	45	6	5横+AE/15B	SOD-323	GBLC15C-N	BORN伯恩半导体
FSNC3D15V1BA	15	16.5	45	6	5横+AE/15B	SOD-323	RLSD32A151C	RUILON(瑞隆源)
FSNC3D15V1BA	15	16.5	45	6	5横+AE/15B	SOD-323	SESD3Z15C	SINO-IC(光宇睿芯)
FSNC3D24V1B	24	26	40	6	2H	SOD-323		
FSNC3D24V1BA	24	26	55	4	5横+AF	SOD-323	PESD1IVN24-AX	Nexperia(安世)
FSNC3D24V1BA	24	26	55	4	5横+AF	SOD-323	PESD24VL1BA, 115	Nexperia(安世)
FSNC3D36V1B	36	38	55	4	2N	SOD-323		
FSNC1524	15/24	16.5/26	25/40	9/6	AM	SOD-323		
FSLC5D5V1B	5	6	12	4	L05B	SOD-523		



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSLC5D5V1U	5	6	15	4	1横+L05U	SOD-523		
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	ESD5Z3. 3T1G	ON(安森美)
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	LESD5Z3. 3T1G	LRC(乐山无线电)
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	ESD5Z3. 3	SHIKUES(时科)
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	ESD5Z3. 3T1G	TECH PUBLIC(台舟)
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	PESD5Z3. 3, 115	Nexperia(安世)
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	ESD3V3D5-TP	MCC(美微科)
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	RLSD52A031V	RUILON(瑞隆源)
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	ESD5Z3. 3	AnBon(台湾安邦)
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	PESDNC5D3V3U	Prisemi 芯导
FSNC5D3V1UA	3.3	4.5	18	16	4横+N1	SOD-523	PESD3V3L1UB, 115	Nexperia(安世)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	ESD5Z5. 0T1G	BORN伯恩半导体
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	CESD5V0D5	CJ(江苏长电/长晶)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	ESD5Z5. 0T1G	ON(安森美)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	CESD3V3D5	CJ(江苏长电/长晶)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	RLSD52A051V	RUILON(瑞隆源)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	PESD5V0S1UB, 115	Nexperia(安世)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	ESD5Z5. 0	SHIKUES(时科)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	ESD5Z5V0	ST(先科)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	LESD5Z5. 0T1G	LRC(乐山无线电)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	ESD5Z5. 0	AnBon(台湾安邦)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	VESD05A1-02V-G-08	VISHAY(威世)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	UC1amp0501H-N	BORN伯恩半导体
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	UCLAMP0501H. TCT	SEMTECH
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	ESD5V0D5-TP	MCC(美微科)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	CESD523NC5VU	CREATEK(达晶微)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	PESD5V0L1UB, 115	Nexperia(安世)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	PESDNC5D5VU	Prisemi 芯导
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	SFD52A05L01	Brightking(台湾君耀)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	PJSD05TS	PANJIT(强茂)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	BSD5A051U	BORN伯恩半导体
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	PESD5Z5.0	Nexperia(安世)
FSNC5D5V1UA	5	6.5	20	15	4横+N2	SOD-523	ESD5Z12.0T1G	BORN伯恩半导体
FSNC5D12V1UA	12	13.3	35	8	4横+N3	SOD-523	CESD12VD5	CJ(江苏长电/长晶)
FSNC5D12V1UA	12	13.3	35	8	4横+N3	SOD-523	LES5Z12T1G	LRC(乐山无线电)
FSNC5D12V1UA	12	13.3	35	8	4横+N3	SOD-523	ESD5Z12T1G	ON(安森美)
FSNC5D12V1UA	12	13.3	35	8	4横+N3	SOD-523	ESD5Z12T1G-N	BORN伯恩半导体
FSNC5D12V1UA	12	13.3	35	8	4横+N3	SOD-523	PESD5Z12, 115	Nexperia(安世)
FSNC5D12V1UA	12	13.3	35	8	4横+N3	SOD-523	SZESD5Z12T1G	ON(安森美)
FSNC5D12V1UA	12	13.3	35	8	4横+N3	SOD-523	PESD12VS1UB	Nexperia(安世)
FSNC5D15V1UA	15	16.5	45	6	4横+N4	SOD-523	ESD5Z15.0T1G	BORN伯恩半导体
FSNC5D15V1UA	15	16.5	45	6	4横+N4	SOD-523	PESD15VS1UB, 115	Nexperia(安世)
FSNC5D15V1UA	15	16.5	45	6	4横+N4	SOD-523	BSD5A151V35	BORN伯恩半导体
FSNC5D24V1UA	24	26	55	4	4横+N5	SOD-523	ESD5Z24.0T1G	BORN伯恩半导体
FSNC5D24V1UA	24	26	55	4	4横+N5	SOD-523	PESD24VS1UB-N	BORN伯恩半导体
FSNC5D24V1UA	24	26	55	4	4横+N5	SOD-523	PESD24VS1UB, 115	Nexperia(安世)
FSNC5D36V1UA	36	40	50	2.5	1横+KT	SOD-523		
FSNC5D3V1BA	3.3	3.8	6	8	CT	SOD-523	LAD52C03L01	Brightking(台湾君耀)
FSNC5D3V1BA	3.3	3.8	6	8	CT	SOD-523	TPAZ5123-01H	TECH PUBLIC(台舟)
FSNC5D3V1BA	3.3	3.8	6	8	CT	SOD-523	ESD5z3.3T	Applied Power(应能微)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC5D3V1BA	3.3	3.8	6	8	CT	SOD-523	ESD5Z3.3C	TECH PUBLIC(台舟)
FSNC5D3V1BA	3.3	3.8	6	8	CT	SOD-523	ESD5Z36	MDD
FSNC5D3V1BA	3.3	3.8	6	8	CT	SOD-523	TPESD5491S	TECH PUBLIC(台舟)
FSNC5D3V1BA	3.3	3.8	6	8	CT	SOD-523	ESD3.3V52D-C	SOCAY(硕凯)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	PESD5VOS1BBN	BORN伯恩半导体
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	LES5D5.0CT1G	LRC(乐山无线电)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	ESD5B5.0ST1G	ON(安森美)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	CESDB5V0D5	CJ(江苏长电/长晶)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	RLSD52A051C	RUILON(瑞隆源)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	ESD5Z5.0C	SHIKUES(时科)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	CESD523NC5VB	CREATEK(达晶微)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	PESD5V0V1BB-N	BORN伯恩半导体
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	PESDNC5D5VB	Prisemi 芯导
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	PESD5V0V1BB, 115	Nexperia(安世)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	SBD52C05L01	Brightking(台湾君耀)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	LES5D5.0CT1G	LRC(乐山无线电)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	PESD5V0U1BB, 115	Nexperia(安世)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	TPAZ5125-01H	TECH PUBLIC(台舟)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	PJSD05CTS	PANJIT(强茂)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	LES5D5.0CT1G	UMW(友台半导体)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	ESD5Z5.0CT1G	TECH PUBLIC(台舟)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	CESD523LC5VB	CREATEK(达晶微)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	SLES5D5.0C	SIkor(萨科微)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	LAD52C05L01	Brightking(台湾君耀)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	SE5D10B5.0A	SEMIWARE(赛米微尔)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	SEN0501D5	SALLTECH(萨瑞)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	SD5C051V	ZHIDE(志得)
FSNC5D5V1BA	5	5.8	6	8	DT/ +5.C8.	SOD-523	SDD52C05L01	Brightking(台湾君耀)
FSNC5D8V1BA	8	9	11	9	8C	SOD-523		
FSNC5D12V1BA	12	13	14	6	12C	SOD-523		
FSNC9D3V1BA	3.3	3.7	7	6	1横+B/批号	SOD-923		
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	RLSD92A031C	RUILON(瑞隆源)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	ESD9B5.0ST5G	ON(安森美)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	PESDNC9D5VB	Prisemi 芯导
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	LES9D5.0CT5G	LRC(乐山无线电)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	RLSD92A051C	RUILON(瑞隆源)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	ESD5V0D9B -	Yint(音特电子)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	ESD9B5VD	TECH PUBLIC(台舟)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	ESD9Z5.0C	AnBon(台湾安邦)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	CESD923NC5VB	CREATEK(达晶微)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	ESD9B3.3ST5G	ON(安森美)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	ESD5V0D9B-TP	MCC(美微科)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	SLES9D5.0CT5G	Slkor(萨科微)
FSNC9D5V1BA	5	6	8.5	6	1横+C/批号	SOD-923	LAD92C5.0L01	Brightking(台湾君耀)
FSNC9D12V1UA	12	15.3	20	16	1横+12W	SOD-923		
FSNC712	7/12	7.5/13.3	19	24	712	SOT-23		
FSNC712A	7/12	7.5/13.3	14~25	17	712	SOT-23	SDT23C712L02	Brightking(台湾君耀)
FSNC712A	7/12	7.5/13.3	14~25	17	712	SOT-23	SM712-02HTG	TECH PUBLIC(台舟)
FSNC712A	7/12	7.5/13.3	14~25	17	712	SOT-23	RLST23A712C	RUILON(瑞隆源)
FSNC712A	7/12	7.5/13.3	14~25	17	712	SOT-23	SM712-TP	MCC(美微科)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC712A	7/12	7.5/13.3	14~25	17	712	SOT-23	MSP712	MSKSEMI(美森科)
FSNC712A	7/12	7.5/13.3	14~25	17	712	SOT-23	SM712	SEMBO(深波)
FSNC712A	7/12	7.5/13.3	14~25	17	712	SOT-23	SM712H-TP	MCC(美微科)
FSNC712A	7/12	7.5/13.3	14~25	17	712	SOT-23	CDSOT23-SM712	BOURNS
FSNC1236	12/36	14/40	32~60	15/3	1236	SOT-23		
FSNC23T3V2U	3.3	4.5	9	32	M03	SOT-23		
FSNC23T3V2UA	3.3	4	8	25	M03	SOT-23		
FSNC23T5V2UC	5	6	9	16	M05	SOT-23	CEST23NC5VU-M	CREATEK(达晶微)
FSNC23T5V2UC	5	6	9	16	M05	SOT-23	MA3075WALT1G	ON(安森美)
FSNC23T5V2UC	5	6	9	16	M05	SOT-23	SM05	UMW(友台半导体)
FSNC23T5V2UC	5	6	9	16	M05	SOT-23	MST23C242V	Me-TECH(美台高科)
FSNC23T5V2UC	5	6	9	16	M05	SOT-23	PSOT05C	Protek Devices
FSNC23T5V2U	5	6	9	30	M05	SOT-23	PESD5V0S2BT	BORN伯恩半导体
FSNC23T5V2U	5	6	9	30	M05	SOT-23	GSOT05C-E3-08	VISHAY(威世)
FSNC23T5V2U	5	6	9	30	M05	SOT-23	PESD5V2S2UT	UMW(友台半导体)
FSNC23T5V2U	5	6	9	30	M05	SOT-23	RLST23A052V	RUILON(瑞隆源)
FSNC23T5V2U	5	6	9	30	M05	SOT-23	SM05.N	BORN伯恩半导体
FSNC23T5V2U	5	6	9	30	M05	SOT-23	HSM05-TP	MCC(美微科)
FSNC23T5V2U	5	6	9	30	M05	SOT-23	SM05T1G	ON(安森美)
FSNC23T5V2UA	5	6	9	15	M05	SOT-23		
FSNC23T5V2UB	5	6	8	10	B 05C	SOT-23		
FSNC23T5V2UC	5	6	9	16	M05	SOT-23		
FSNC23T5V2UD	5	6.5	8.5	20	M05	SOT-23		
FSNC23T7V2U	7	7.5	11	25	M07	SOT-23	MMBZ6V8A	ON(安森美)
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	SM12T1G	ON(安森美)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	LGSOT12CLT1G	LRC(乐山无线电)
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	SET23A12L02-E18	Brightking(台湾君耀)
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	ESDA14V2L	BORN伯恩半导体
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	PESD12VS2UT, 215	Nexperia(安世)
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	CESD12VAP	CJ(江苏长电/长晶)
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	PESD12VS2UT	UMW(友台半导体)
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	RLST23A122V	RUILON(瑞隆源)
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	CEST23NC12VU	CREATEK(达晶微)
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	SM12. N	BORN伯恩半导体
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	SM12	UMW(友台半导体)
FSNC23T12V2U	12	13.5	18	15	M12	SOT-23	PSOT12C	Protek Devices
FSNC23T12V2UA	12	13.5	15	10	12C	SOT-23		
FSNC23T15V2U	15	16.5	22	11	M15	SOT-23	MMBZ18VALT1G	ON(安森美)
FSNC23T15V2U	15	16.5	22	11	M15	SOT-23	PESD15VS2UT	UMW(友台半导体)
FSNC23T15V2U	15	16.5	22	11	M15	SOT-23	SM15. N	BORN伯恩半导体
FSNC23T15V2U	15	16.5	22	11	M15	SOT-23	SM15H-TP	MCC(美微科)
FSNC23T15V2U	15	16.5	22	11	M15	SOT-23	PSOT15C	Protek Devices
FSNC23T15V2UA	15	16.5	19	7	15C	SOT-23		
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	PESD1CAN	UMW(友台半导体)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	PESD5V2S2UT, 215	Nexperia(安世)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	PESD2CAN	UMW(友台半导体)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	ESDA25L	ST(意法半导体)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	ESDA25L	BORN伯恩半导体
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	SET23A24L02	Brightking(台湾君耀)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	PESD24VS2UT, 215	Nexperia(安世)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	PESD24VS2UT	UMW(友台半导体)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	RLST23A242V	RUILON(瑞隆源)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	SM24.N	BORN伯恩半导体
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	SM24B-TP	MCC(美微科)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	GSOT24C-E3-08	VISHAY(威世)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	PSOT24C	TECH PUBLIC(台舟)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	ESDOP8RFL E6327	Infineon(英飞凌)
FSNC23T24V2U	24	26.5	33	6	M24	SOT-23	ESDOP4RFL E6327	Infineon(英飞凌)
FSNC23T24V2UA	24	26.5	30	4	M24	SOT-23		
FSNC23T36V2U	36	40	55	3	M36	SOT-23		
FSNC23T3V2B	3.3	4.5	8.5	24	C03	SOT-23		
FSNC23T3V2BA	3.3	4.5	8.5	16	C03	SOT-23		
FSNC23T3V2BB	3.3	3.6	8	24	C03	SOT-23		
FSNC23T3V2BC	3.3	3.6	8	30	C03	SOT-23		
FSNC23T5V2B	5	6.5	9.5	20	C05	SOT-23		
FSNC23T5V2BA	5	6.5	9.5	15	C05	SOT-23		
FSNC23T5V2BB	5	5.5	6.5	8	V3W/14	SOT-23		
FSNC23T8V2B	8	8.5	11	15	C08	SOT-23		
FSNC23T8V2BA	8	8.5	11	12	C07	SOT-23		
FSNC23T12V2B	12	13.3	20	12	C12/AB2	SOT-23	TPD2E007DCKR	TI(德州仪器)
FSNC23T12V2B	12	13.3	20	12	C12/AB2	SOT-23	RLST23A122C	RUILON(瑞隆源)
FSNC23T12V2B	12	13.3	20	12	C12/AB2	SOT-23	PESD12VL2BT-TP	TECH PUBLIC(台舟)
FSNC23T12V2B	12	13.3	20	12	C12/AB2	SOT-23	SM12-TP	MCC(美微科)
FSNC23T12V2B	12	13.3	20	12	C12/AB2	SOT-23	SM12B-TP	MCC(美微科)
FSNC23T12V2B	12	13.3	20	12	C12/AB2	SOT-23	CESDBLC12VAP	CJ(江苏长电/长晶)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC23T12V2B	12	13.3	20	12	C12/AB2	SOT-23	PESD15VL2BTN	BORN伯恩半导体
FSNC23T12V2BA	12	13.3	20	8	C12	SOT-23		
FSNC23T15V2B	15	16.5	25	9	C15/BB2	SOT-23	SM15C	AnBon(台湾安邦)
FSNC23T15V2B	15	16.5	25	9	C15/BB2	SOT-23	SM15B-TP	MCC(美微科)
FSNC23T15V2B	15	16.5	25	9	C15/BB2	SOT-23	CESDBLC15VAP	CJ(江苏长电/长晶)
FSNC23T15V2B	15	16.5	25	9	C15/BB2	SOT-23	PESD15VL2BT, 215	Nexperia(安世)
FSNC23T15V2BA	15	16.5	25	6	C15	SOT-23		
FSNC23T18V2B	18	19.5	30	7	C18	SOT-23		
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	NUP2125WTT1G	ON(安森美)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	PESD24VL2BTN	BORN伯恩半导体
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	TPESD1CAN	TECH PUBLIC(台舟)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	PESD2CAN	TECH PUBLIC(台舟)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	SDT23C24L02	Brightking(台湾君耀)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	ESD2105L	MDD
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	TPCDSOT23-T24CAN	TECH PUBLIC(台舟)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	ESD二极管	FUXINSEMI(富芯微)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	RLST23A242C	RUILON(瑞隆源)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	TPSM24CANB-02HTG	TECH PUBLIC(台舟)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	S-LR2105LT1G	LRC(乐山无线电)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	NUP2105LT1G-MS	MSKSEMI(美森科)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	SDT23C24L02-AT	Brightking(台湾君耀)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	TPESDCAN24-2BLY	TECH PUBLIC(台舟)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	ESDONCAN1LT3G	ON(安森美)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	SM24BHE3-TP	MCC(美微科)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	PEC3124C2A-AU	PANJIT(强茂)



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ESD静电浪涌保护二极管

型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	NUP2105LT1G-TP	TECH PUBLIC(台舟)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	PESD2IVN24-TR	Nexperia(安世)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	PESD1CAN, 215	Nexperia(安世)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	PESD2CAN, 215	Nexperia(安世)
FSNC23T24V2B	24	26	40	6	C24/CB2/27EY	SOT-23	PESD1CAN	BORN伯恩半导体
FSNC23T24V2B	24	26.5	36	8	CB2/27EY	SOT-23		
FSNC23T24V2BA	24	26.5	40	4	SCH/C24	SOT-23		
FSNC23T36V2B	36	38	55	4	C36	SOT-23		
FSLC23T3V2BA	3.3	4.5	8.5	19	BW3	SOT-23		
FSLC23T5V2BA	5	6.5	9	15	BW5	SOT-23		
FSLC23T8V2BA	8	8.5	12	14	BW8	SOT-23		
FSLC23T12V2BA	12	13.3	19	7	BWA	SOT-23		
FSLC23T15V2BA	15	16.5	24	6	BWC	SOT-23		
FSLC23T24V2BA	24	26	34	4	BWF	SOT-23		
FSLC23T5V2U	5	6	10	4	R22	SOT-23	UBT23A05L02	Brightking(台湾君耀)
FSLC23T5V2U	5	6	10	4	R22	SOT-23	PESD23T5VU	DIOTEC/德欧泰克
FSLC23T5V2U	5	6	10	4	R22	SOT-23	ESD5302F	WILLSEMI(韦尔)
FSLC23T5V2UB	5	6	15	8	UR22	SOT-23		
FSNC2X3V1BB	3.3	3.7	7	6	B	DFN0603-2L		
FSNC2X5V1B	5	6	9	4	G	DFN0603-2L		
FSNC2X5V1BA	5	5.6	8	6	H	DFN0603-2L		
FSNC2X8V1BA	8	9	13	6	J	DFN0603-2L		
FSNC2X12V1BA	12	13.5	16	6	K	DFN0603-2L		
FSLC2F3V1B	3.3	4.5	12	4	1横+S	DFN1006-2L		
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	RCLAMP0521PATCT	SEMTECH



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RWM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPESD8L3.3CT5G	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	Rclamp0521p.tct	SEMTECH
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPRCLAMP3321P	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPPESD3V3X1BL	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	Rclamp0531T-N	BORN伯恩半导体
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	ESD7951ST5G	BORN伯恩半导体
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	PESDUC2FD5VB	Prisemi 芯导
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPESDLC0521P	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	ESD5V0B03-1006	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	PESDMC2FD5VB	Prisemi 芯导
FSLC2F5V1B	5	6	12	4	R1	DFN1006-2L	BDFN2C051U	BORN伯恩半导体
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	ESD0501BL	MDD
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPPESD5V0F1BL	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	ESDSL5V0LB-TP	MCC(美微科)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPESD8L5.0CT5G	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	SE10F10B5.0MA	SEMIWARE(赛米微尔)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPESD5V3U1U-02LRH	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPESD0531T	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	RCLAMP0521P-P	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	PESD5V0U1BL-TP	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	R1	DFN1006-2L	BSDFN2C051U	BORN伯恩半导体
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPPESD5V0X1BCAL	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPSP3022-01ETG	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPESD8LS5.0CT5G	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPAZ5425-01F	TECH PUBLIC(台舟)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPD1E6B06DPLR-TP	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	AZ5425-01F	晶炎
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	ESD5V0B06G-1006	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPESD9N5BM	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	SLESD5.0U035	Slkor(萨科微)
FSLC2F5V1B	5	6	12	4	JJ/ZZ	DFN1006-2L	PESD5V0F1BL	安世
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	SBX0521P	SEMBO(深波)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	TPA0Z8131DI-05L	TECH PUBLIC(台舟)
FSLC2F5V1B	5	6	12	4	JJ/ZZ	DFN1006-2L	PESD5V0F1BLD, 315	Nexperia(安世)
FSLC2F5V1B	5	6	12	4	JJ/ZZ	DFN1006-2L	PESD5V0F1BRLDYL	Nexperia(安世)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	ULC3311CDN	Leiditech(雷卯电子)
FSLC2F5V1B	5	6	12	4	JJ	DFN1006-2L	AZ5413-01F. R7GR	AMAZING(晶焱)
FSLC2F5V1B	5	6	12	4	JJ/UV	DFN1006-2L	LES8L5.0CBT5G	LRC(乐山无线电)
FSLC2F5V1B	5	6	12	4	JJ/4M	DFN1006-2L	ESD8472MUT5G	ON(安森美)
FSLC2F5V1B	5	6	12	4	JJ/6J	DFN1006-2L	SMF05C	ON(安森美)
FSLC2F5V1BA	5	5.5	8.5	3	1横+5T	DFN1006-2L		
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	ESD5311N-TP	TECH PUBLIC(台舟)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	ESD5301N-TP	TECH PUBLIC(台舟)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	TPUCLAMP0501T	TECH PUBLIC(台舟)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	CESD1006LC5VU	CREATEK(达晶微)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	ESD0501L	MDD
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	PESDXC2FD5VU	Prisemi 芯导
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	TPESD9X5VU	TECH PUBLIC(台舟)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	PESDSC2FD5VU	Prisemi 芯导
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	PESDLC2FD5VUH	Prisemi 芯导



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	TPESD9X5VL	TECH PUBLIC(台舟)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	VBUS051BD-HD1-TP	TECH PUBLIC(台舟)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	TPESD5301N	TECH PUBLIC(台舟)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	SP3030-01ETG	TECH PUBLIC(台舟)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	TPAZ5215-01F	TECH PUBLIC(台舟)
FSLC2F5V1U	5	6	12	4	1横+5L	DFN1006-2L	ESD9X5VU-2/TR	WILLSEMI(韦尔)
FSLC2X5V1B	5	6	12	4	5L	DFN0603-2L		
FSLC2X5V1U	5	6	10	4	1横+L5	DFN0603-2L		
FSNC2F12V1BA	12	13.5	16	6	AF	DFN1006-2L	CESD1006NC12VB-M	CREATEK(达晶微)
FSNC2F12V1BA	12	13.5	16	6	AF	DFN1006-2L	UC1amp1211P-N	BORN伯恩半导体
FSNC2F12V1BA	12	13.5	16	6	AF	DFN1006-2L	ESD12010C	MDD
FSNC2F12V1BA	12	13.5	16	6	AF	DFN1006-2L	BDFN2C181R	BORN伯恩半导体
FSNC2F12V1BA	12	13.5	16	6	AF	DFN1006-2L	TPESD203-B1-02EL	TECH PUBLIC(台舟)
FSNC2F12V1BA	12	13.5	16	6	AF	DFN1006-2L	PJSD12LCFN2	PANJIT(强茂)
FSNC2F12V1BA	12	13.5	16	6	AF	DFN1006-2L	ESDLC12VLB-TP	MCC(美微科)
FSNC2F12V1BA	12	13.5	16	6	AF	DFN1006-2L	ESD8V0L1B-02LRH-TP	TECH PUBLIC(台舟)
FSNC2F12V1BA	12	13.5	16	6	AF	DFN1006-2L	ESD9N12BA	TECH PUBLIC(台舟)
FSNC2F12V1U	12	14	20	20	1横+U12	DFN1006-2L		
FSNC2F12V1UA	12	13.5	20	10	1横+12	DFN1006-2L		
FSNC2F15V1BA	15	16.5	22	7	1横+E	DFN1006-2L		
FSNC2F15V1UA	15	16.5	22	7	1横+15	DFN1006-2L		
FSNC2F3V1BA	3.3	4.5	7	6	1横+T	DFN1006-2L		
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	TPESD3V3V1BL	TECH PUBLIC(台舟)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	TPUCLAMP3311P	TECH PUBLIC(台舟)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	ESD0402DFN1006 3.3V	PTTC(聚鼎)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	SES3V3D1006SY-2B	Semitel (晶讯)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	PJSD03LCFN2	PANJIT (强茂)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	BDFN2C3R31V	BORN伯恩半导体
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	TPE03GBP2	TECH PUBLIC (台舟)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	TPAZ5123-01F	TECH PUBLIC (台舟)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	TPDESD3V3S1BL	TECH PUBLIC (台舟)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	ESDL3V3LB-TP	MCC (美微科)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	AU3321P1	Applied Power (应能微)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	AZ5013-01F. R7G	AMAZING (晶焱)
FSNC2F3V1BB	3.3	3.7	7	6	1横+T	DFN1006-2L	AZ5123-01F. R7GR	AMAZING (晶焱)
FSNC2F3V1BC	3.3	3.8	5	20	1横+ES	DFN1006-2L		
FSNC2F3V1UA	3.3	5	7	20	1横+3	DFN1006-2L		
FSNC2F5V1B	5	6	9	4	1横+UB	DFN1006-2L	ESD9B5VL	TECH PUBLIC (台舟)
FSNC2F5V1B	5	6	9	4	1横+UB	DFN1006-2L	TPAZ5325-01F	TECH PUBLIC (台舟)
FSNC2F5V1B	5	6	9	4	1横+UB	DFN1006-2L	ESD0801PB	MDD
FSNC2F5V1B	5	6	9	4	1横+UB	DFN1006-2L	TPUCLAMP0511T	TECH PUBLIC (台舟)
FSNC2F5V1B	5	6	9	4	1横+UB	DFN1006-2L	SLESD8D5. 0C	S1kor (萨科微)
FSNC2F5V1B	5	6	9	4	1横+UB	DFN1006-2L	ESD5V0B100A-1006	TECH PUBLIC (台舟)
FSNC2F5V1B	5	6	9	4	1横+UB	DFN1006-2L	MKT312U035 停产	MK (米客方德)
FSNC2F5V1B	5	6	9	4	1横+UB	DFN1006-2L	PESD5V0S1BLN-MS	MSKSEMI (美森科)
FSNC2F5V1B	5	6	9	4	1横+UB	DFN1006-2L	SESDFBP05CL	SINO-IC (光宇睿芯)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	MKT3412AB 停产	MK (米客方德)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	ESD5451N-TP	TECH PUBLIC (台舟)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	PESDNC2FD5VB	Prisemi 芯导
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	PESDNC2FD5VBS	Prisemi 芯导



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	CLAMP0551P1	WPMtek(维攀微)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	ESD5451X-TP	TECH PUBLIC(台舟)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	TPESD8D5. 0CT5G	TECH PUBLIC(台舟)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	TPESD9N5B	TECH PUBLIC(台舟)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	RLSD92Q051C	RUILON(瑞隆源)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	PESD5V0V1BL-TP	TECH PUBLIC(台舟)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	SES5VD1006SHSY-2B	Semitel(晶讯)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	ESD 0402 DFN1006 6.3V	PTTC(聚鼎)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	PESD5V0G1BLYL	Nexperia(安世)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	PJSD05LCFN2_R1	PANJIT(强茂)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	JEB05DF	JJW(捷捷微)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	ESD5V0B15G-0201	TECH PUBLIC(台舟)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	ESDLC5V0L2B-TP	MCC(美微科)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	MKT312N15 停产	MK(米客方德)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	PESD05NFA-MS	MSKSEMI(美森科)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	TPAZ5725-01F	TECH PUBLIC(台舟)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	ESD5471X-TP	TECH PUBLIC(台舟)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	TESDBLC5V0LED02	CJ(江苏长电/长晶)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	DTESDB5V0LED02	CJ(江苏长电/长晶)
FSNC2F5V1BA	5	6	8	6	PB/. H/C/. S	DFN1006-2L	LES8D5. 0CKT5G	LRC(乐山无线电)
FSNC2F5V1BB	5	6	9	15	D5	DFN1006-2L		
FSNC2F5V1UA	5	6	10	15	1横+YB	DFN1006-2L		
FSNC2F5V1UB	5	6	9.5	22	D5	DFN1006-2L		
FSNC2F7V1UA	7	8	11	12	1横+7	DFN1006-2L		
FSNC2F8V1BA	8	9	13	6	2横+R2C	DFN1006-2L	BDFN2C071V	BORN伯恩半导体



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC2F8V1BA	8	9	13	6	2横+R2C	DFN1006-2L	PESDNC2FD7VBL	Prisemi 芯导
FSNC2F8V1BA	8	9	13	6	2横+R2C	DFN1006-2L	TPESD5411N	TECH PUBLIC(台舟)
FSNC2F8V1BA	8	9	13	6	2横+R2C	DFN1006-2L	PESDNC2FD8VB	Prisemi 芯导
FSNC2F8V1BA	8	9	13	6	2横+R2C	DFN1006-2L	PESDNC2FD7VB	Prisemi 芯导
FSNC2F8V1BA	8	9	13	6	2横+R2C	DFN1006-2L	ESD7V0LB-TP	MCC(美微科)
FSNC2F8V1BA	8	9	13	6	2横+R2C	DFN1006-2L	ESDA07CP	Leiditech(雷卯电子)
FSNC2F8V1BA	8	9	13	6	2横+R2C	DFN1006-2L	VCUT0714A-HD1-GS08	VISHAY(威世)
FSNC2F24V1BA	24	26	35	4	DH	DFN1006-2L	PESDNC2FD24VB	Prisemi 芯导
FSNC2F24V1BA	24	26	35	4	DH	DFN1006-2L	BDFN2A241V35	BORN伯恩半导体
FSNC2F24V1BA	24	26	35	4	DH	DFN1006-2L	PESD24VS1UL-N	BORN伯恩半导体
FSNC2F24V1BA	24	26	35	4	DH	DFN1006-2L	BDFN2C241V35	BORN伯恩半导体
FSNC2F24V1BA	24	26	35	4	DH	DFN1006-2L	ESD24VB35-1006	TECH PUBLIC(台舟)
FSNC2F24V1U	24	26	33	7	1横+24	DFN1006-2L		
FSNC2F24V1UA	24	26.6	35	4	1横+24	DFN1006-2L		
FSLC3F5V2U	5	6	20.5	4	1横+L05	DFN1006-3L		
FSNC3F3V2BB	3.3	3.7	7	6	3B	DFN1006-3L		
FSNC3F5V2BA	5	5.6	8	6	5B	DFN1006-3L		
FSNC16F5V1BA	5	5.5	7.5	100	3X	DFN1610-2L		
FSHC16F4V1U	4.5	5.5	6.5	100	1横+H4	DFN1610-2L		
FSHC16F5V1U	5	6	7	100	1横+H5	DFN1610-2L		
FSHC16F7V1UA	7	7.5	6.5	100	1横+H7	DFN1610-2L		
FSHC16F12V1U	12	13.3	15	70	1横+H12	DFN1610-2L		
FSHC16F15V1U	15	16.5	18	60	1横+H15	DFN1610-2L		
FSHC16F18V1U	18	19.5	25	50	1横+H18	DFN1610-2L		
FSHC16F26V1U	26	28	35	40	1横+H26	DFN1610-2L		



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSHC3F5V1U	5	6	7.5	300		DFN2X2-3L		
FSHC3F7V1U	7	8	9	200		DFN2X2-3L		
FSHC3F10V1U	10	12	13.5	200		DFN2X2-3L		
FSHC3F12V1U	12	13.3	15	180		DFN2X2-3L		
FSHC3F15V1U	15	16.5	18.5	130		DFN2X2-3L		
FSHC3F24V1U	24	26	30	100		DFN2X2-3L		
FSUC2X5V1B	5	6	15	3	5U	DFN0603-2L		
FSUC2X5V1BA	5	6	15	3	空白	DFN0603-2L		
FSUC2F5V1B	5	6	15	3	NL	DFN1006-2L		
FSUC06F5V2U	5	6	8.5	4	.0522P	DFN1610-6	RCLAMP0522P-TP	TECH PUBLIC(台舟)
FSUC06F5V2U	5	6	8.5	4	.0522P	DFN1610-6	RCLAMP0522P.TCT	UMW(友台半导体)
FSUC06F5V2U	5	6	8.5	4	.0522P	DFN1610-6	MSESD0522P	MSKSEMI(美森科)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	TESD5V0V4UA RDG	Taiwan Semiconductor(台湾半导体)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	ESD0524P	MDD
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	PESDALC10N5VU	Prisemi 芯导
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	TPD4E05U06DQAR-TP	TECH PUBLIC(台舟)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	ESD5304D-MS	MSKSEMI(美森科)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	0524P	YANGJIE(扬杰)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	CESD2510LC5VU-M	CREATEK(达晶微)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	TPSP3012-04UTG	TECH PUBLIC(台舟)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	SBC0524P	SEMBO(深波)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	TPESDR0524PMUTAG	TECH PUBLIC(台舟)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	ESDA6V8UD-MS	MSKSEMI(美森科)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	MKT642U05 停产	MK(米客方德)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	RCLAMP0524P-MS	MSKSEMI(美森科)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	ULC0524P	TECH PUBLIC(台舟)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	ESD5344D-MS	MSKSEMI(美森科)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	MSULC0524P	MSKSEMI(美森科)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	MS1045-04F	MSKSEMI(美森科)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	UBQ10A05L04HI	Brightking(台湾君耀)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	IP4292CZ10-TBR, 115	Nexperia(安世)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	IP4294CZ10-TBR, 115	Nexperia(安世)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	AZ1045-04F	AMAZING(晶焱)
FSUC10F5V4U	5	6	8.5	4	.0524P	DFN2510-10L	WS05-4R2P	WAYON/维安
FSUC10F5V4UA	5	6	8	4.5	.0524P	DFN2510-10L		
FSUC10F3V4U	3.3	4	8.5	4.5	.3324P	DFN2510-10L	TPAZ1143-04F	TECH PUBLIC(台舟)
FSUC10F3V4U	3.3	4	8.5	4.5	.3324P	DFN2510-10L	TPRCLAMP3324P	TECH PUBLIC(台舟)
FSUC10F3V4U	3.3	4	8.5	4.5	.3324P	DFN2510-10L	SESUC3V3D2510-10U	Semitel(晶讯)
FSUC10F3V4U	3.3	4	8.5	4.5	.3324P	DFN2510-10L	TPESD3324PA	TECH PUBLIC(台舟)
FSUC10F3V4U	3.3	4	8.5	4.5	.3324P	DFN2510-10L	ESDLC3304P5-TP	MCC(美微科)
FSUC10F3V4U	3.3	4	8.5	4.5	.3324P	DFN2510-10L	UBQ10A03L04	Brightking(台湾君耀)
FSUC10F3V4U	3.3	4	8.5	4.5	.3324P	DFN2510-10L	ESD3V3U4ULC-MS	MSKSEMI(美森科)
FSLC523T5V2U	5	6	10	4	P5	SOT-523	RCLAMP0502BATCT	SEMTECH
FSLC523T5V2U	5	6	10	4	P5	SOT-523	UAT52A05L02	Brightking(台湾君耀)
FSNC353T5V4UB	5	6	10	8	.W. E/S	SOT-353		
FSNC363T5V5UB	5	6	9.5	8	.5C	SOT-363	SMF15CT1G	ON(安森美)
FSNC363T5V5UB	5	6	9.5	8	.5C	SOT-363	SMF05CT1G-MS	MSKSEMI(美森科)
FSNC363T5V5UB	5	6	9.5	8	.5C	SOT-363	LESDA6V1W6T1G	LRC(乐山无线电)
FSNC363T5V5UB	5	6	9.5	8	.5C	SOT-363	SAT36A05L05	Brightking(台湾君耀)
FSNC363T5V5UB	5	6	9.5	8	.5C	SOT-363	SEMF05LCC	SINO-IC(光宇睿芯)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSNC363T5V5UB	5	6	9.5	8	.5C	SOT-363	CESD5VOK5	CJ (江苏长电/长晶)
FSNC363T5V5UB	5	6	9.5	8	.5C	SOT-363	SMF05CT2G	ON(安森美)
FSNC363T5V5UB	5	6	9.5	8	.5C	SOT-363	PESD5VOL5UYF	Nexperia(安世)
FSLC353T5V4UA	5	6	8.5	4.5	.A54	SOT-353		
FSLC363T5V4UA	5	6	8.5	4	.B54	SOT-363	RCLAMP0504FATCT-N	BORN伯恩半导体
FSLC363T5V4UA	5	6	8.5	4	.B54	SOT-363	RCLAMP0504F	Semtech(升特)
FSLC363T5V4U	5	6	10	4	.B54	SOT-363		
FSLC523T5V2U	5	6	8	4	P5	SOT-563		
FSLC563T5V2U	5	6	8	4	.A	SOT-563		
FSLC563T5V4U	5	6	8	4	.空白待定	SOT-563		
FSUC236T5V4U	5	6	9	4.5	.V05/.4D	SOT23-6	PRTR5V0U4D, 125	Nexperia(安世)
FSUC236T5V4U	5	6	9	4.5	.V05/.UL46	SOT23-6	USBLC6-4SC6	ST(意法半导体)
FSUC236T5V4U	5	6	9	4.5	.V05/.U5H4	SOT23-6	ESDU5V0H4	CJ (江苏长电/长晶)
FSUC236T5V4U	5	6	9	4.5	.V05	SOT23-6	SESRV05-4	SEMIWARE(赛米微尔)
FSUC236T5V4U	5	6	9	4.5	.V05/.V5L	SOT23-6	BST236A054U	BORN伯恩半导体
FSUC236T5V4U	5	6	9	4.5	.V05	SOT23-6	AZC099-04F	晶焱-Amazing
FSUC236T5V4U	5	6	9	4.5	.V05/.F54	SOT23-6	RCLAMP0504F	Semtech(升特)
FSUC236T5V4U	5	6	9	4.5	.V05/.MMWW	SOT23-6	ESDA6V8UW	WILLSEMI(韦尔)
FSUC236T5V4U	5	6	9	4.5	.V05/.P4HH	SOT23-6	PDWL050019	TECH PUBLIC(台舟)
FSUC236T5V4UB	5	6	10	5.5	.V05	SOT23-6		
FSLC236T5V2U	5	6	8.5	4	.UL26	SOT23-6		
FSLC236T5V2UA	5	6	10	4.5	.UL26	SOT23-6	USBLC6-2SC6	ST(意法半导体)
FSLC236T5V2UA	5	6	10	4.5	.UL26	SOT23-6	USBLC6-2SC6	TECH PUBLIC(台舟)
FSLC236T5V2UA	5	6	10	4.5	.UL26	SOT23-6	MSUSBLC6-2SC6	MSKSEMI(美森科)
FSLC236T5V2UA	5	6	10	4.5	.UL26	SOT23-6	UBT26A05L03	Brightking(台湾君耀)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V _{RRM} (V)	V _{BR} (V)	V _C (V)	I _{PP} (A)	Marking	Package	型号	品牌
FSLC236T5V2UA	5	6	10	4.5	.UL26	SOT23-6	TPESD0502S6	TECH PUBLIC(台舟)
FSLC236T5V2UA	5	6	10	4.5	.UL26	SOT23-6	MAX3207EAUT+T	MAXIM(美信)
FSNC236T5V4UA	5	6	9	22	.S05	SOT23-6		
FSNC236T5V4UB	5	6	8	12	.ES61	SOT23-6		
FSNC236T5V4UC	5	6	8	23	.空白	SOT23-6		
FSNC236T7V4UA	7	7.5	11	20	.S07	SOT23-6		
FSNC236T12V4UA	12	13	18	15	.S12	SOT23-6		
FSNC236T15V4UA	15	16	25	12	.S15	SOT23-6		
FSNC236T5V5UA	5	6	9	22	.S05	SOT23-6		
FSNC236T7V5UA	7	7.5	11	20	.S07	SOT23-6		
FSNC236T12V5UA	12	13	18	15	.S12	SOT23-6		
FSNC236T15V5UA	15	16	25	12	.S15	SOT23-6		
FSLC143T5V2UA	5	6	10	6	R05	SOT-143	UDT14A05L03	Brightking(台湾君耀)
FSLC143T5V2UA	5	6	10	6	R05	SOT-143	CM1213A-02SR	ON(安森美)
FSLC143T5V2UA	5	6	10	6	R05	SOT-143	SR05	SEMBO(深波)
FSLC143T5V2UA	5	6	10	6	R05	SOT-143	PESD2ETH-AXR	Nexperia(安世)
FSLC143T5V2UA	5	6	10	6	R05	SOT-143	MSSR05.TCT	MSKSEMI(美森科)
FSLC2.8	2.8	3	5	20	U2.8	SOT-23		
FSLC2.8-4	2.8	3	5	20	SLVU2.8-4	SOP-8	SLVU2.8-4-TP	TECH PUBLIC(台舟)
FSLC2.8-4	2.8	3	5	20	SLVU2.8-4	SOP-8	TPE08A2.8L04	TECH PUBLIC(台舟)
FSLC2.8-4	2.8	3	5	20	SLVU2.8-4	SOP-8	TPAZ3028-04P.RDG	TECH PUBLIC(台舟)
FSLC2.8-4	2.8	3	5	20	SLVU2.8-4	SOP-8	SLVU2.8-8-LF-T7	PROTEK
FSLC2.8-4	2.8	3	5	20	SLVU2.8-4	SOP-8	UFS08A2.8L04	Brightking(台湾君耀)
FSLC2.8-4	2.8	3	5	20	SLVU2.8-4	SOP-8	RLS08A2.84LV	RUILON(瑞隆源)
FSLC2.8-4	2.8	3	5	20	SLVU2.8-4	SOP-8	SLVU2.8-4-TP	MCC(美微科)



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型号	工作电压	击穿电压	钳位电压	浪涌电流	印字	封装	代替型号	
Type	V_{RWM} (V)	V_{BR} (V)	V_C (V)	I_{PP} (A)	Marking	Package	型号	品牌
FSLC2.8-4	2.8	3	5	20	SLVU2.8-4	SOP-8	UFS08C2.8L04	Brightking(台湾君耀)